# **Supplementary information**

# High-yield production of mono- or few-layer transition metal dichalcogenide nanosheets by an electrochemical lithium ion intercalation-based exfoliation method

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## Supplementary information

### for

High-yield production of mono- or few- layer transition metal dichalcogenides nanosheets by electrochemical lithium ion intercalation-based exfoliation method

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Supplementary Figure 1 Galvanostatic discharge curve for (a) MoS<sub>2</sub>, (b) WS<sub>2</sub>, (c) TiS<sub>2</sub>,
(d) TaS<sub>2</sub>, (e) BN, (f) NbSe<sub>2</sub>. Adapted with permission from ref. <sup>1-3</sup>.



**Supplementary Figure 2** (a) Photographs of the exfoliated  $MoS_2$  nanosheets, which were not fully exfoliated, and some of the bulk particles can be clearly seen. (b) Unsatisfactory AFM image of the exfoliated  $MoS_2$  nanosheets, in which lots of particles are observed.



**Supplementary Figure 3** (a) TEM image of the exfoliated  $ZrS_2$  nanosheets. (b) AFM image of the exfoliated  $ZrS_2$  nanosheets, showing the average thickness of ~0.9 nm. (c) TEM image of the exfoliated graphene nanosheets. (d) AFM image of the exfoliated graphene nanosheets, showing the average thickness of ~1.0 nm. (e) SEM image of the exfoliated WSe<sub>2</sub> nanosheets. (f) AFM image of the exfoliated WSe<sub>2</sub> nanosheets, showing the average of the exfoliated WSe<sub>2</sub> nanosheets, showing the average thickness of ~2.7 nm. (g) SEM image of the exfoliated Sb<sub>2</sub>Se<sub>3</sub> nanosheets. (h) SEM image of the exfoliated Bi<sub>2</sub>Se<sub>3</sub> nanosheets. Adapted with permission from ref. <sup>1,2</sup>.



Supplementary Figure 4 SEM images of (a) bulk MoS<sub>2</sub>, (b) bulk WS<sub>2</sub>, (c) bulk TiS<sub>2</sub>,(d) bulk TaS<sub>2</sub>, (e) bulk BN, (f) bulk NbSe<sub>2</sub>.



**Supplementary Figure 5** SEM images of the exfoliated (a)  $MoS_2$ , (b)  $WS_2$ , (c)  $TiS_2$ , (d)  $TaS_2$ , (e) BN, (f) NbSe<sub>2</sub> nanosheets. Note that TMDs nanosheets shows the darker contrast in comparison with SiO<sub>2</sub> substrate since the conductivity of TMDs nanosheet are better than SiO<sub>2</sub> substrate, while BN shows white or lighter contrast.



**Supplementary Figure 6** SEM images of the large area TMDs nanosheets deposited on Si/SiO<sub>2</sub> substrate: (a, b) MoS<sub>2</sub>, (c, d) TiS<sub>2</sub>, (e, f) TaS<sub>2</sub> nanosheets. Note that TMDs nanosheets shows the darker contrast in comparison with SiO<sub>2</sub> substrate since the conductivity of TMD nanosheets are better than SiO<sub>2</sub> substrate.



**Supplementary Figure 7** EDS of the exfoliated  $MoS_2$  (a),  $WS_2$  (b),  $TiS_2$  (c),  $TaS_2$  (d) nanosheets deposited on  $Si/SiO_2$  substrate.



**Supplementary Figure 8** Photoluminescence spectrum of a single-layer  $MoS_2$  nanosheet deposited on Si/SiO<sub>2</sub> substrate. After the nanosheet was annealed at 450 oC in Ar gas for 2 h, it was excited with 488 nm laser in air at room temperature to give the PL spectrum. Adapted with permission from ref. <sup>1</sup>.



**Supplementary Figure 9** Temperature-dependent Seebeck coefficient (a), electrical conductivity (b) and powder factor (c) for NbSe<sub>2</sub> nanosheet and bulk material. Adapted with permission from ref. <sup>2</sup>.

**Supplementary Table 1** The molecular weights of different layered compounds, and the corresponding discharge capacities as lithium-ion batteries with one lithium ion intercalated, i.e., LiMN.

Layered compound	Molecular weight (g∙mol <sup>-1</sup> )	Capacity(1 Li) = LiMN (mAh·g <sup>-1</sup> )	
MoS <sub>2</sub>	160	167.2	
$WS_2$	248	107.9	
TiS <sub>2</sub>	112	238.9	
$TaS_2$	245	109.2	
$ZrS_2$	155	172.5	
Graphite	12	2229.6	
BN	25	1070.2	
NbSe <sub>2</sub>	251	106.6	

**Supplementary Table 2** Summary of the characteristics of the exfoliated 2D materials in this protocol.

Materials	MoS <sub>2</sub>	$WS_2$	TiS <sub>2</sub>	$TaS_2$	BN	NbSe <sub>2</sub>
Thickness	10102	1.0	16102	$0.0 \pm 0.1$	4.0	2.4
(nm)	$1.0 \pm 0.2$	1.0	$1.0 \pm 0.2$	$0.9 \pm 0.1$	4.0	2.4
Lateral						
dimensions	0.3-3.0	0.4-1.0	0.3-3.0	0.3-3.0	1.0	1.0
(µm)						
Yield	92%	-	93%	93%	-	-

#### **Supplementary References**

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